Epitaxial Growth of Y-stabilized ZrO₂ Buffer Layers for YBCO Coated Conductor by MOCVD

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Y-stabilized ZrO₂(YSZ) buffer layers for YBCO coated conductors were deposited on MgO the single crystal and bi-axially textured NiO/Ni and CeO₂/Ni substrates by metal organic chemical vapor deposition, using Y(thd)₃ and Zr(thd)₄. To establish the deposition condition of YSZ, deposition temperature and oxygen flow rate were changed at constant working pressure of 10 Torr. The texture and the surface roughness were estimated by X-ray pole figure and atomic force microscopy. When YSZ was deposited on MgO single crystal, (200)texture was developed at 660 °C~800 °C at oxygen flow rate of 100~500 sccm. When using CeO₂/Ni substrate, (200) texture was obtained at deposition temperature of 740 °C at oxygen flow rate of 300 sccm. The surface roughness increased with increasing deposition temperature. And the FWHMs of in-plane and out-of-plane of the YSZ films on the single crystal MgO were fairly good as 1° and 5°, respectively.

keywords: MOCVD, YSZ, NiO/Ni & CeO2/Ni substrate, coated conductors

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